

NTS1045EMFS, NRVTS1045EMFS

Exceptionally Low Leakage Trench-based Schottky Rectifier

Features

- Fine Lithography Trench-based Schottky Technology for Very Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- NRV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free and Halide-Free Devices

Typical Applications

- Switching Power Supplies including Wireless, Smartphone and Notebook Adapters
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

Mechanical Characteristics:

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in.
- Lead Finish: 100% Matte Sn (Tin)
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Device Meets MSL 1 Requirements

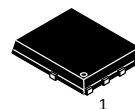


ON Semiconductor®

<http://onsemi.com>

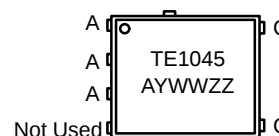
SCHOTTKY BARRIER RECTIFIERS 10 AMPERES 45 VOLTS

1,2,3  5,6



SO-8 FLAT LEAD
CASE 488AA
STYLE 2

MARKING DIAGRAM



TE1045 = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping†
NTS1045EMFST1G	SO-8 FL (Pb-Free)	1500 / Tape & Reel
NTS1045EMFST3G	SO-8 FL (Pb-Free)	5000 / Tape & Reel
NRVTS1045EMFST1G	SO-8 FL (Pb-Free)	1500 / Tape & Reel
NRVTS1045EMFST3G	SO-8 FL (Pb-Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NTS1045EMFS, NRVTS1045EMFS

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	45	V
Average Rectified Forward Current (Rated V_R , $T_C = 166^\circ\text{C}$)	$I_{F(AV)}$	10	A
Peak Repetitive Forward Current, (Rated V_R , Square Wave, 20 kHz, $T_C = 162^\circ\text{C}$)	I_{FRM}	20	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I_{FSM}	210	A
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$
Operating Junction Temperature	T_J	-55 to +150	$^\circ\text{C}$
Unclamped Inductive Switching Energy (10 mH Inductor, Non-repetitive)	E_{AS}	100	mJ
ESD Rating (Human Body Model)		3B	
ESD Rating (Machine Model)		M4	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Typ	Max	Unit
Thermal Resistance, Junction-to-Case, Steady State (Assumes 600 mm ² 1 oz. copper bond pad, on a FR4 board)	$R_{\theta JC}$	–	2.0	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS

Instantaneous Forward Voltage (Note 1) ($i_F = 5.0$ Amps, $T_J = 25^\circ\text{C}$) ($i_F = 10$ Amps, $T_J = 25^\circ\text{C}$) ($i_F = 5.0$ Amps, $T_J = 125^\circ\text{C}$) ($i_F = 10$ Amps, $T_J = 125^\circ\text{C}$)	V_F	0.42 0.48 0.34 0.41	– 0.60 – 0.53	V
Reverse Current (Note 1) (Rated dc Voltage, $T_J = 25^\circ\text{C}$) (Rated dc Voltage, $T_J = 125^\circ\text{C}$)	i_R	20 7.0	50 20	μA mA
Diode Capacitance (Rated dc Voltage, $T_J = 25^\circ\text{C}$, $f = 1$ MHz)	C_d	300		pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

TYPICAL CHARACTERISTICS

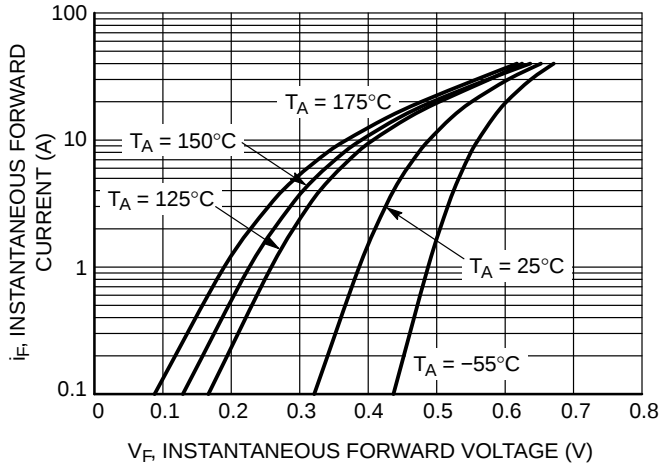


Figure 1. Typical Instantaneous Forward Characteristics

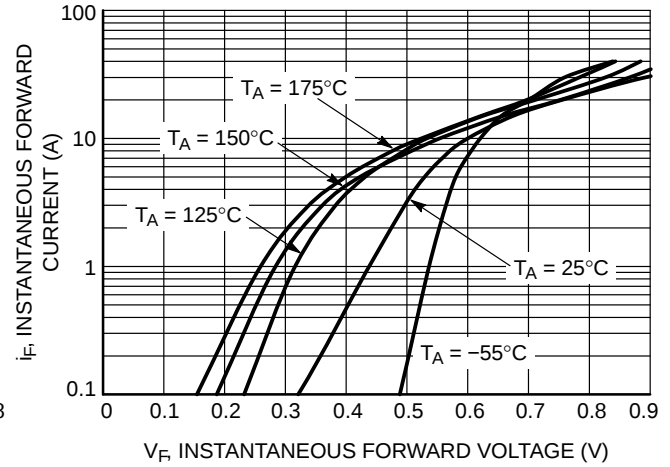


Figure 2. Maximum Instantaneous Forward Characteristics

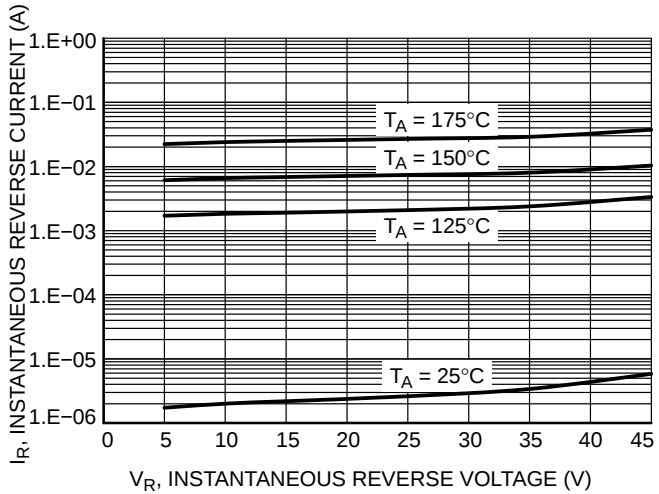


Figure 3. Typical Reverse Characteristics

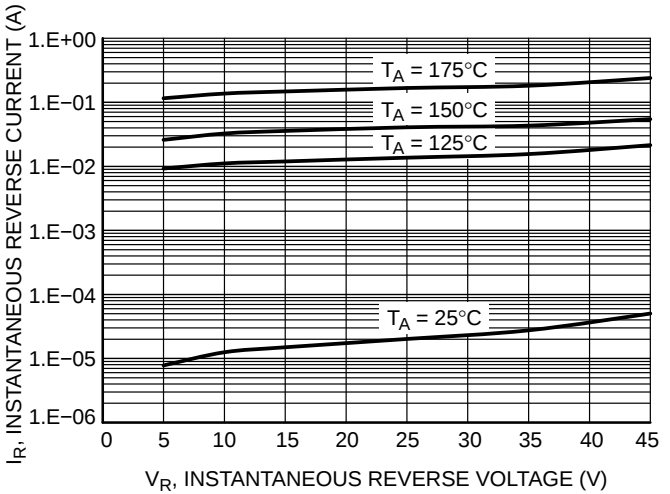


Figure 4. Maximum Reverse Characteristics

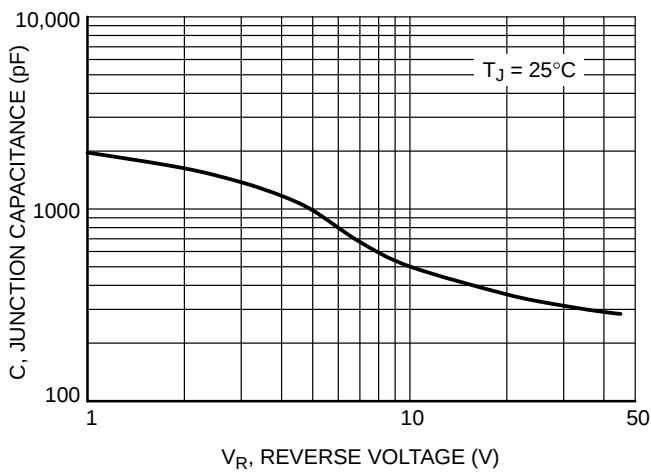


Figure 5. Typical Junction Capacitance

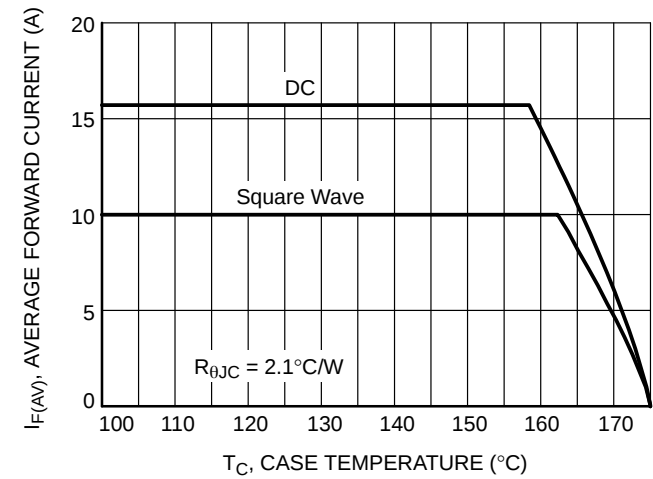


Figure 6. Current Derating

TYPICAL CHARACTERISTICS

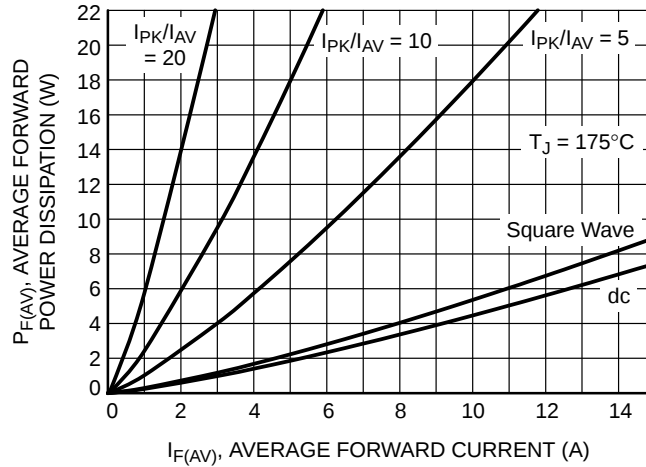


Figure 7. Forward Power Dissipation

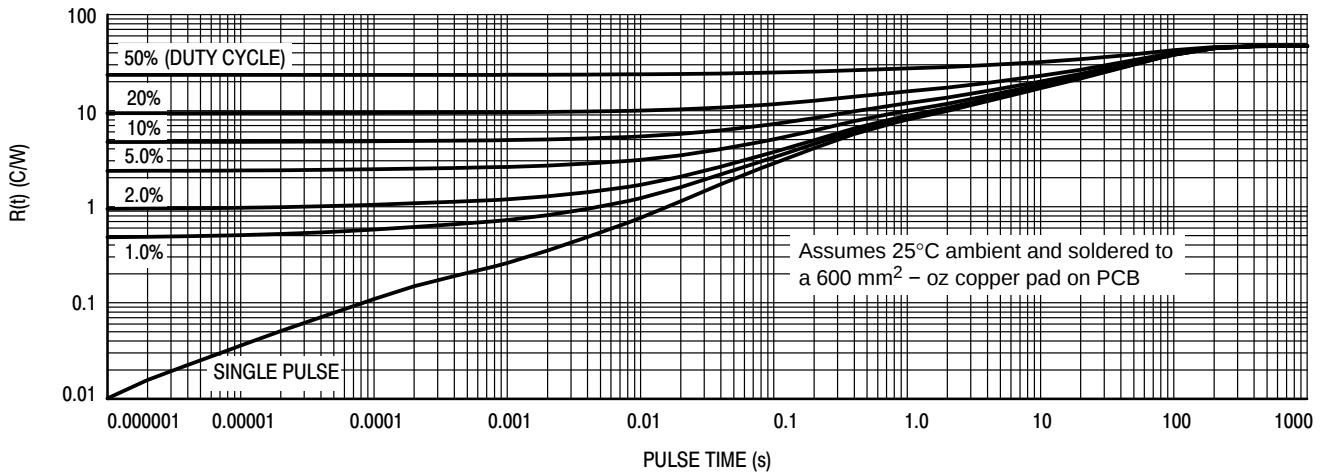


Figure 8. Typical Thermal Characteristics

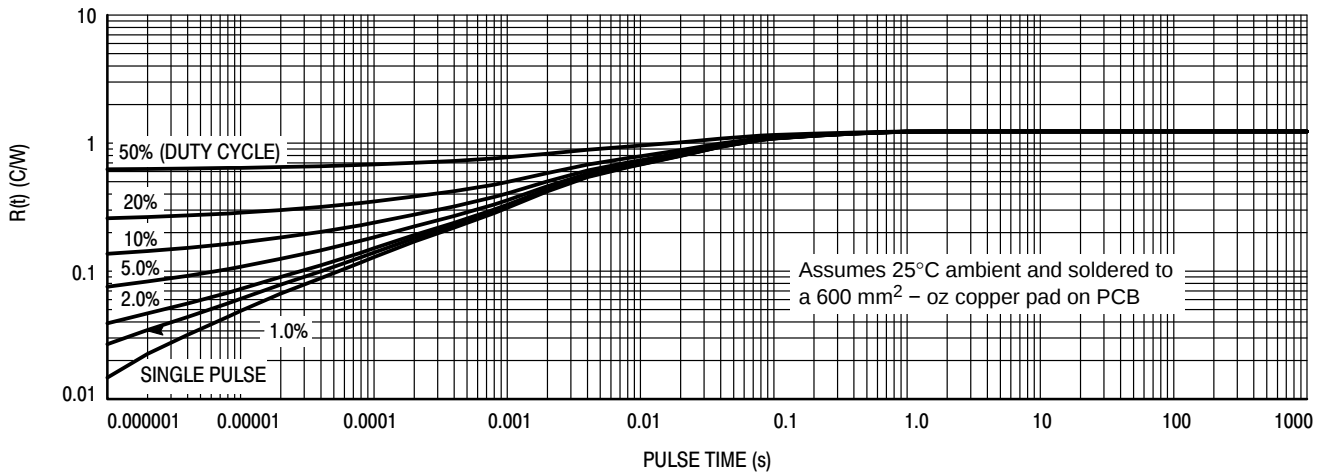


Figure 9. Typical Transient Thermal Response Characteristics, Junction-to-Case

NTS1045EMFS, NRVTS1045EMFS

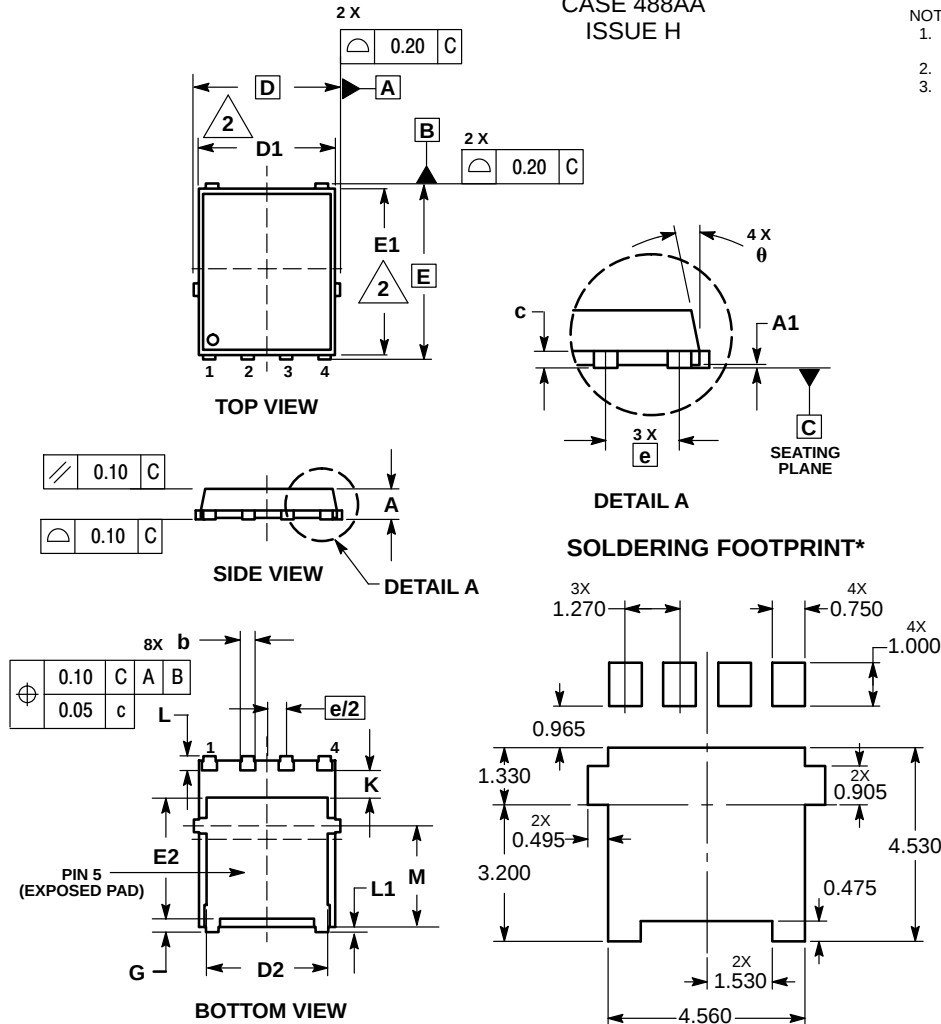
PACKAGE DIMENSIONS

DFN5 5x6, 1.27P
(SO-8FL)
CASE 488AA
ISSUE H

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.15 BSC		
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.15 BSC		
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.61	0.71
K	1.20	1.35	1.50
L	0.51	0.61	0.71
L1	0.05	0.17	0.20
M	3.00	3.40	3.80
θ	0°	---	12°



STYLE 2:

1. ANODE
2. ANODE
3. ANODE
4. NO CONNECT
5. CATHODE

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and the are registered trademarks of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries. SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3867 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local Sales Representative

NTS1045EMFS/D

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9